Ann Witvrouw

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#	Paper	IF	Citations
155	The Use of Functionally Graded Poly-SiGe Layers for MEMS Applications. <i>Materials Science Forum</i> , 2005 , 492-493, 255-260	0.4	202
154	Bulk and interface stresses in silver-nickel multilayered thin films. <i>Journal of Applied Physics</i> , 1993 , 74, 2517-2523	2.5	132
153	Experimental determination of the maximum post-process annealing temperature for standard CMOS wafers. <i>IEEE Transactions on Electron Devices</i> , 2001 , 48, 377-385	2.9	99
152	Viscosity and elastic constants of amorphous Si and Ge. <i>Journal of Applied Physics</i> , 1993 , 74, 7154-7161	2.5	98
151	On the influence of laser defocusing in Selective Laser Melting of 316L. <i>Additive Manufacturing</i> , 2018 , 23, 161-169	6.1	86
150	Keyhole-induced porosities in Laser-based Powder Bed Fusion (L-PBF) of Ti6Al4V: High-fidelity modelling and experimental validation. <i>Additive Manufacturing</i> , 2019 , 30, 100835	6.1	78
149	Comparison between wet HF etching and vapor HF etching for sacrificial oxide removal 2000 , 4174, 130)	55
148	Materials issues in the processing, the operation and the reliability of MEMS. <i>Microelectronic Engineering</i> , 2004 , 76, 245-257	2.5	47
147	Creep characterization of Al alloy thin films for use in MEMS applications. <i>Microelectronic Engineering</i> , 2004 , 76, 272-278	2.5	38
146	Creep as a reliability problem in MEMS. <i>Microelectronics Reliability</i> , 2004 , 44, 1733-1738	1.2	36
145	Poly SiGe, a promising material for MEMS monolithic integration with the driving electronics. <i>Sensors and Actuators A: Physical</i> , 2002 , 97-98, 503-511	3.9	35
144	Creep-resistant aluminum alloys for use in MEMS. <i>Journal of Micromechanics and Microengineering</i> , 2005 , 15, S165-S170	2	31
143	CMOSMEMS integration today and tomorrow. <i>Scripta Materialia</i> , 2008 , 59, 945-949	5.6	30
142	Determination of the plane stress elastic constants of thin films from substrate curvature measurements: Applications to amorphous metals. <i>Journal of Applied Physics</i> , 1993 , 73, 7344-7350	2.5	29
141	New low-stress PECVD poly-SiGe Layers for MEMS. <i>Journal of Microelectromechanical Systems</i> , 2003 , 12, 816-825	2.5	27
140	Characterization and strain gradient optimization of PECVD poly-SiGe layers for MEMS applications. <i>Sensors and Actuators A: Physical</i> , 2006 , 130-131, 403-410	3.9	23
139	Effect of in situ boron doping on properties of silicon germanium films deposited by chemical vapor deposition at 400 °C. Journal of Materials Research, 2001, 16, 2607-2612	2.5	22

138	Why CMOS-integrated transducers? A review. Microsystem Technologies, 2000, 6, 192-199	1.7	22
137	Characterization of KrF excimer laser annealed PECVD SixGe1 for MEMS post-processing. <i>Sensors and Actuators A: Physical</i> , 2006 , 127, 316-323	3.9	20
136	Stable thin film encapsulation of acceleration sensors using polycrystalline silicon as sacrificial and encapsulation layer. <i>Sensors and Actuators A: Physical</i> , 2004 , 114, 355-361	3.9	20
135	. Journal of Microelectromechanical Systems, 2010 , 19, 202-214	2.5	19
134	The viscosity of amorphous metallic thin films. <i>Materials Science & Description of Engineering A: Structural Materials: Properties, Microstructure and Processing</i> , 1991 , 134, 1274-1277	5.3	19
133	CMOS-Integrated Poly-SiGe Piezoresistive Pressure Sensor. <i>IEEE Electron Device Letters</i> , 2012 , 33, 1204-	-1 ₄ 2. p 6	18
132	Fabrication of Porous Membranes for MEMS Packaging by One-Step Anodization in Sulfuric Acid. Journal of the Electrochemical Society, 2007 , 154, K74	3.9	18
131	CMOS compatible polycrystalline silicongermanium based pressure sensors. <i>Sensors and Actuators A: Physical</i> , 2012 , 188, 9-18	3.9	16
130	Poly-SiGe-Based MEMS Thin-Film Encapsulation. <i>Journal of Microelectromechanical Systems</i> , 2012 , 21, 110-120	2.5	15
129	Physics. The best materials for tiny, clever sensors. <i>Science</i> , 2004 , 306, 986-7	33.3	15
129	Physics. The best materials for tiny, clever sensors. <i>Science</i> , 2004 , 306, 986-7 Improving the selectivity by using different blocking agents in DNA hybridization assays for SiGe bio-molecular sensors. <i>Microelectronic Engineering</i> , 2013 , 111, 421-424	33·3 2.5	15
	Improving the selectivity by using different blocking agents in DNA hybridization assays for SiGe	2.5	
128	Improving the selectivity by using different blocking agents in DNA hybridization assays for SiGe bio-molecular sensors. <i>Microelectronic Engineering</i> , 2013 , 111, 421-424	2.5	14
128	Improving the selectivity by using different blocking agents in DNA hybridization assays for SiGe bio-molecular sensors. <i>Microelectronic Engineering</i> , 2013 , 111, 421-424 MEMS packaging and reliability: An undividable couple. <i>Microelectronics Reliability</i> , 2012 , 52, 2228-2234	2.5	14
128 127 126	Improving the selectivity by using different blocking agents in DNA hybridization assays for SiGe bio-molecular sensors. <i>Microelectronic Engineering</i> , 2013 , 111, 421-424 MEMS packaging and reliability: An undividable couple. <i>Microelectronics Reliability</i> , 2012 , 52, 2228-2234 Stress Relaxation in Alūu and AlBiūu Thin Films. <i>Journal of Materials Research</i> , 1999 , 14, 1246-1254	2.5	14 14
128 127 126	Improving the selectivity by using different blocking agents in DNA hybridization assays for SiGe bio-molecular sensors. <i>Microelectronic Engineering</i> , 2013 , 111, 421-424 MEMS packaging and reliability: An undividable couple. <i>Microelectronics Reliability</i> , 2012 , 52, 2228-2234 Stress Relaxation in Alūu and AlBiūu Thin Films. <i>Journal of Materials Research</i> , 1999 , 14, 1246-1254 Ultra-high density MEMS probe memory device. <i>Microelectronic Engineering</i> , 2010 , 87, 1198-1203 Highly reliable CMOS-integrated 11MPixel SiGe-based micro-mirror arrays for high-end industrial	2.5	14 14 14
128 127 126 125	Improving the selectivity by using different blocking agents in DNA hybridization assays for SiGe bio-molecular sensors. <i>Microelectronic Engineering</i> , 2013 , 111, 421-424 MEMS packaging and reliability: An undividable couple. <i>Microelectronics Reliability</i> , 2012 , 52, 2228-2234 Stress Relaxation in Altu and Albitu Thin Films. <i>Journal of Materials Research</i> , 1999 , 14, 1246-1254 Ultra-high density MEMS probe memory device. <i>Microelectronic Engineering</i> , 2010 , 87, 1198-1203 Highly reliable CMOS-integrated 11MPixel SiGe-based micro-mirror arrays for high-end industrial applications 2008 , Mechanical characterization of poly-SiGe layers for CMOSMEMS integrated application. <i>Journal of</i>	2.5 - 1.2 - 2.5	14 14 14 13

120	Improvement of PECVD Silicontermanium Crystallization for CMOS Compatible MEMS Applications. <i>Journal of the Electrochemical Society</i> , 2010 , 157, D103	3.9	11
119	Simultaneous Optimization of the Material Properties, Uniformity and Deposition Rate of Polycrystalline CVD and PECVD Silicon-Germanium Layers for MEMS Applications. <i>ECS Transactions</i> , 2009 , 16, 353-364	1	11
118	CMOS-MEMS Integration: Why, How and What?. <i>IEEE/ACM International Conference on Computer-Aided Design, Digest of Technical Papers</i> , 2006 ,		11
117	Electromigration-induced drift in damascene and plasma-etched Al(Cu). I. Kinetics of Cu depletion in polycrystalline interconnects. <i>Journal of Applied Physics</i> , 2000 , 87, 86-98	2.5	11
116	Above-IC generic poly-SiGe thin film wafer level packaging and MEM device technology: Application to accelerometers 2011 ,		10
115	Determination Of Elastic Constants And Viscosity Of Amorphous Thin Films From Substrate Curvature. <i>Materials Research Society Symposia Proceedings</i> , 1990 , 188, 147		10
114	Multi-response optimization of ultrathin poly-SiGe films characteristics for Nano-ElectroMechanical Systems (NEMS) using the grey-Taguchi technique. <i>Microelectronic Engineering</i> , 2013 , 111, 229-233	2.5	9
113	(Invited) SiGe MEMS Technology: A Platform Technology Enabling Different Demonstrators. <i>ECS Transactions</i> , 2010 , 33, 799-812	1	9
112	Development, Optimization and Evaluation of a CF4 Pretreatment Process to Remove Unwanted Interfacial Layers in Stacks of CVD and PECVD Polycrystalline Silicon-Germanium for MEMS Applications. <i>ECS Transactions</i> , 2010 , 28, 79-90	1	9
111	. Journal of Microelectromechanical Systems, 2007 , 16, 581-588	2.5	9
110	Determination of stress profile and optimization of stress gradient in PECVD poly-SiGe films. <i>Sensors and Actuators A: Physical</i> , 2005 , 118, 313-321	3.9	9
109	Viscosity, Structural Relaxation and Defect Annihilation Kinetics of Amorphous Si. <i>Materials Research Society Symposia Proceedings</i> , 1990 , 205, 21		9
108	Dielectrophoretic assembly of suspended single-walled carbon nanotubes. <i>Microelectronic Engineering</i> , 2012 , 98, 218-221	2.5	8
107	Outgassing study of thin films used for poly-SiGe based vacuum packaging of MEMS. <i>Microelectronics Reliability</i> , 2011 , 51, 1878-1881	1.2	8
106	SLM device for 193nm lithographic applications. <i>Microelectronic Engineering</i> , 2009 , 86, 569-572	2.5	8
105	An in-plane SiGe differential capacitive accelerometer for above-IC integration. <i>Journal of Micromechanics and Microengineering</i> , 2011 , 21, 074011	2	8
104	The influence of addition elements on the early resistance changes observed during electromigration testing of Al metal lines. <i>Microelectronics Reliability</i> , 1998 , 38, 87-98	1.2	8
103	Kinetic to Transport-Limited Anhydrous HF Etching of Silicon Oxynitride Films in Supercritical CO2. Journal of Physical Chemistry C, 2007 , 111, 15251-15257	3.8	8

102	A 10 fh thick poly-SiGe gyroscope processed above 0.35 fh CMOS 2007 ,		8
101	Fabrication and reliability testing of Ti/TiN heaters 1999,		8
100	Light sensitive SiGe MEM resonator for detection and frequency tuning applications. 2010,		7
99	A CMOS compatible polycrystalline silicon-germanium based piezoresistive pressure sensor 2011 ,		7
98	Stress relaxation in Al(Cu) thin films. <i>Microelectronic Engineering</i> , 1997 , 33, 137-147	2.5	7
97	CMOS-MEMS integration. <i>IEEE/ACM International Conference on Computer-Aided Design, Digest of Technical Papers</i> , 2006 ,		7
96	Thin film encapsulation of acceleration sensors using polysilicon sacrificial layers		7
95	Poly-SiGe, a superb material for MEMS. <i>Materials Research Society Symposia Proceedings</i> , 2003 , 782, 1		7
94	Effect of deposition parameters on the stress gradient of CVD and PECVD poly-SiGe for MEMS applications 2004 ,		7
93	Characterization of Reduced-pressure Chemical Vapor Deposition Polycrystalline Silicon Germanium Deposited at Temperatures B50 LC. <i>Journal of Materials Research</i> , 2002 , 17, 1580-1586	2.5	7
92	Quantifying the Aggregation Factor in Carbon Nanotube Dispersions by Absorption Spectroscopy. Journal of Nanoscience, 2014 , 2014, 1-13		6
91	Towards CMOS-compatible single-walled carbon nanotube resonators. <i>Microelectronic Engineering</i> , 2013 , 107, 219-222	2.5	6
90	Improvement of the poly-SiGe electrode contact technology for MEMS. <i>Journal of Micromechanics and Microengineering</i> , 2010 , 20, 095029	2	6
89	Stiction-free poly-SiGe resonators for monolithic integration of biosensors with CMOS 2011 ,		6
88	Effect of oxide and W-CMP on the material properties and electromigration behaviour of layered aluminum metallisations. <i>Microelectronic Engineering</i> , 2000 , 50, 291-299	2.5	6
87	Improving the quality of up-facing inclined surfaces in laser powder bed fusion of metals using a dual laser setup. <i>Procedia CIRP</i> , 2020 , 94, 266-269	1.8	5
86	Influence of germanium incorporation on the structural and electrical properties of boron-doped ultrathin poly-Si1 Ge x films deposited by chemical vapour deposition. <i>Applied Physics A: Materials Science and Processing</i> , 2014 , 116, 751-757	2.6	5
85	SiGe MEMS at processing temperatures below 250°C. Sensors and Actuators A: Physical, 2012, 188, 230-	 23 <i>9</i>)	5

84	Dedicated test structure for the measurement of adhesion forces between contacting surfaces in MEMS devices 2013 ,		5	
83	Packaging of 11 MPixel CMOS-Integrated SiGe Micro-Mirror Arrays 2009 ,		5	
82	Long-term reliability measurements on MEMS using a laser-Doppler vibrometer 2008,		5	
81	High throughput measurement techniques for wafer level yield inspection of MEMS devices 2008,		5	
80	A new generic surface micromachining module for MEMS hermetic packaging at temperatures below 200 LC. <i>Microsystem Technologies</i> , 2007 , 13, 1451-1456	1.7	5	
79	Highly reliable and extremely stable SiGe micro-mirrors 2007,		5	
78	Influence of the anti reflective coating on the electromigration resistance of 0.5 h technology metal-2 line structures. <i>Applied Surface Science</i> , 1995 , 91, 208-214	6.7	5	
77	The isocurrent test: A promising tool for wafer-level evaluation of the interconnect reliability. <i>Microelectronics Reliability</i> , 1996 , 36, 1847-1850	1.2	5	
76	Elastic Constants and Viscosity of Amorphous PdSi/PdSiFe Multilayers. <i>Materials Research Society Symposia Proceedings</i> , 1991 , 239, 121		5	
75	Thermal simulation of the cooling down of selective laser sintered parts in PA12. <i>Rapid Prototyping Journal</i> , 2018 , 24, 1117-1123	3.8	5	
74	Thickness effect on the structural and electrical properties of poly-SiGe films. <i>Materials Research Bulletin</i> , 2014 , 49, 102-107	5.1	4	
73	SiGe MEMS Accelerometers Combining a Large Bandwidth with a High Capacitive Sensitivity. <i>Procedia Engineering</i> , 2012 , 47, 742-745		4	
72	Effect of the functionalization process on the performance of SiGe MEM resonators used for bio-molecular sensing. <i>Microelectronics Reliability</i> , 2012 , 52, 2272-2277	1.2	4	
71	Physical loss mechanisms for resonant acoustical waves in boron doped poly-SiGe deposited with hydrogen dilution. <i>Journal of Applied Physics</i> , 2010 , 108, 084517	2.5	4	
70	Wafer Level Characterization of the Sacrificial HDP Oxide Lateral Etching by Anhydrous Vapor HF with Ethanol Vapor for SiGe MEMS Structures. <i>ECS Transactions</i> , 2010 , 33, 295-307	1	4	
69	Design and characterization of a CMOS compatible poly-SiGe lowg capacitive accelerometer. <i>Procedia Engineering</i> , 2010 , 5, 742-745		4	
68	Study of Cu diffusion in an Alflwt.%Sif.5wt.%Cu bond pad with an Alflwt.%Si bond wire attached using scanning electron microscopy. <i>Microelectronics Reliability</i> , 1998 , 38, 309-315	1.2	4	
67	Determination of the piezoresistivity of microcrystalline silicon-germanium and application to a pressure sensor 2008 ,		4	

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66	The influence of geometrical imperfections in micromachined cantilevers on the extracted Young@ modulus using a simple model. <i>Journal of Micromechanics and Microengineering</i> , 2008 , 18, 115027	2	4
65	The Road To Flexible Mems Integration. <i>Materials Research Society Symposia Proceedings</i> , 2008 , 1075, 1		4
64	Wafer level characterization and failure analysis of microsensors and actuators 2008,		4
63	Optimisation of PECVD poly-SiGe layers for MEMS post-processing on top of CMOS		4
62	Metal induced crystallization of SiGe at 370°C for monolithically integrated MEMS applications. <i>Materials Research Society Symposia Proceedings</i> , 2004 , 808, 12		4
61	Effect of Deposition Conditions on the Structural and Mechanical Properties of Poly SiGe. <i>Materials Research Society Symposia Proceedings</i> , 2000 , 609, 851		4
60	The Effect of the Passivation Material on the Stress and Stress Relaxation Behavior of Narrow Al-Si-Cu Lines. <i>Materials Research Society Symposia Proceedings</i> , 1996 , 428, 519		4
59	Static and dynamic characterization of pull-in protected CMOS compatible poly-SiGe grating light valves. <i>Sensors and Actuators A: Physical</i> , 2012 , 179, 283-290	3.9	3
58	Comparison of three methods to measure the internal pressure of empty MEMS packages 2012,		3
57	Meta-materials approach to sensitivity enhancement of MEMS BAW resonant sensors 2013,		3
56	Apparent and steady-state etch rates in thin film etching and under-etching of microstructures: II. Characterization. <i>Journal of Micromechanics and Microengineering</i> , 2010 , 20, 055034	2	3
55	Apparent and steady-state etch rates in thin film etching and under-etching of microstructures: I. Modelling. <i>Journal of Micromechanics and Microengineering</i> , 2010 , 20, 055033	2	3
54	Evaluation of the piezoresistive and electrical properties of polycrystalline silicon-germanium for MEMS sensor applications 2010 ,		3
53	Sealing of poly-SiGe surface micromachined cavities for MEMS-above-CMOS applications. <i>Journal of Micromechanics and Microengineering</i> , 2011 , 21, 115019	2	3
52	Thin film encapsulated SiGe accelerometer for MEMS above IC integration 2011,		3
51	Investigation of temporary stiction in poly-SiGe micromirror arrays 2011,		3
50	SiGe based grating light valves: A leap towards monolithic integration of MOEMS. <i>Microelectronic Engineering</i> , 2010 , 87, 1195-1197	2.5	3
49	Sputtered Tantalum as a Structural Material for Surface Micromachined RF Switches. <i>Materials Research Society Symposia Proceedings</i> , 2002 , 729, 331		3

48	Electromigration-Induced Drift in Damascene vs. Conventional Interconnects: An Intrinsic Difference. <i>Materials Research Society Symposia Proceedings</i> , 1998 , 516, 89	3
47	Modeling and microstructural characterization of incubation, time-dependent drift and saturation during electromigration in AlBiCu stripes. <i>Microelectronics Reliability</i> , 1999 , 39, 1603-1616	3
46	The viscosity of amorphous Pd-Si and Pd-Si/Pd-Si-Fe multilayers determined from stress relaxation in thin films on a substrate. <i>Journal of Applied Physics</i> , 1994 , 75, 1456-1462	3
45	The Detrimental Effect of a Passivation on the Electromigration Lifetime of Narrow Al-Si-Cu Lines. <i>Materials Research Society Symposia Proceedings</i> , 1995 , 391, 447	3
44	Investigation of temporary stiction in poly-SiGe micromirror arrays. <i>Sensors and Actuators A: Physical</i> , 2012 , 188, 320-328	2
43	Stacked Boron Doped Poly-Crystalline Silicon-Germanium Layers: an Excellent MEMS Structural Material. <i>Materials Research Society Symposia Proceedings</i> , 2008 , 1075, 1	2
42	Micromachining of pulsed laser annealed PECVD Si/sub x/Ge/sub 1-x/ deposited at temperatures /spl les/ 370/spl deg/C	2
41	Self-aligned 0-level sealing of MEMS devices by a two layer thin film reflow process	2
40	SIGEM, low-temperature deposition of poly-SiGe MEMs structures on standard CMOS circuits (Invited Paper) 2005 ,	2
39	Planarization of deep trenches 2001 , 4557, 49	2
39	Planarization of deep trenches 2001, 4557, 49 Integration of HSQ in the direct-on-metal approach for 0.25-fh technology. <i>Microelectronic Engineering</i> , 2000, 50, 349-355 2.5	2
	Integration of HSQ in the direct-on-metal approach for 0.25-th technology. <i>Microelectronic</i>	
38	Integration of HSQ in the direct-on-metal approach for 0.25-fit technology. <i>Microelectronic Engineering</i> , 2000 , 50, 349-355 A 2D MEMS grating based CMOS compatible poly-SiGe variable optical attenuator. <i>Microelectronic</i>	2
38 37	Integration of HSQ in the direct-on-metal approach for 0.25-fh technology. <i>Microelectronic Engineering</i> , 2000 , 50, 349-355 A 2D MEMS grating based CMOS compatible poly-SiGe variable optical attenuator. <i>Microelectronic Engineering</i> , 2013 , 105, 8-12 2.5	2
38 37 36	Integration of HSQ in the direct-on-metal approach for 0.25-fin technology. <i>Microelectronic Engineering</i> , 2000 , 50, 349-355 A 2D MEMS grating based CMOS compatible poly-SiGe variable optical attenuator. <i>Microelectronic Engineering</i> , 2013 , 105, 8-12 Poly-SiGe for MEMS-above-CMOS Sensors. <i>Springer Series in Advanced Microelectronics</i> , 2014 , 1	2 1 1
38 37 36 35	Integration of HSQ in the direct-on-metal approach for 0.25-fih technology. <i>Microelectronic Engineering</i> , 2000 , 50, 349-355 A 2D MEMS grating based CMOS compatible poly-SiGe variable optical attenuator. <i>Microelectronic Engineering</i> , 2013 , 105, 8-12 Poly-SiGe for MEMS-above-CMOS Sensors. <i>Springer Series in Advanced Microelectronics</i> , 2014 , 1 2012,	2 1 1
38 37 36 35 34	Integration of HSQ in the direct-on-metal approach for 0.25-fit technology. <i>Microelectronic Engineering</i> , 2000 , 50, 349-355 A 2D MEMS grating based CMOS compatible poly-SiGe variable optical attenuator. <i>Microelectronic Engineering</i> , 2013 , 105, 8-12 Poly-SiGe for MEMS-above-CMOS Sensors. <i>Springer Series in Advanced Microelectronics</i> , 2014 , 2012, Study of glass frit induced stiction using a micromirror array. <i>Microelectronics Reliability</i> , 2012 , 52, 2256-2266	2 1 1 1

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30	Influence of the novel anchor design on the shear strength of poly-sige thin film wafer level packages 2010 ,		1
29	CMOS-integrated sige MEMS: Application to micro-mirrors 2009 ,		1
28	Evaluation of the Electrical Properties, Piezoresistivity and Noise of poly-SiGe for MEMS-above-CMOS applications. <i>Materials Research Society Symposia Proceedings</i> , 2009 , 1153, 1		1
27	Polycrystalline Silicon-Germanium Electrode Contact Technology Improvement for MEMS Applications. <i>Materials Research Society Symposia Proceedings</i> , 2009 , 1222, 1		1
26	Laser-induced Crystallization of SiGe MEMS Structural Layers Deposited at Temperatures below 250°C. Materials Research Society Symposia Proceedings, 2009, 1153, 1		1
25	A wafer-level poly-sige-based thin film packaging technology demonstrated on a soi-based high-Q MEM resonator 2011 ,		1
24	Novel micromirror design with variable pull-in voltage. <i>Microelectronic Engineering</i> , 2010 , 87, 1248-1252	2 2.5	1
23	Overview of the kinetics of the early stages of electromigration under low (= realistic) current density stress. <i>Microelectronics Reliability</i> , 1998 , 38, 1009-1013	1.2	1
22	A novel gap narrowing process for creating high aspect ratio transduction gaps for MEM HF Resonators. <i>Materials Research Society Symposia Proceedings</i> , 2008 , 1139, 1		1
21	Self-aligned 0-level sealing of MEMS devices by a two layer thin film reflow process. <i>Microsystem Technologies</i> , 2004 , 10, 364-371	1.7	1
20	Comparison of the Electromigration Behavior of Al(MgCu) with Al(Cu) and Al(SiCu). <i>Materials Research Society Symposia Proceedings</i> , 1998 , 514, 133		1
19	The kinetics of the early stages of electromigration and concurrent temperature induced processes in thin film metallisations studied by means of an in-situ high resolution resistometric technique. <i>Microelectronics Reliability</i> , 1999 , 39, 1657-1665	1.2	1
18	Effect of Cu on Al Interfacial Mass Transport in Bamboo Rie and Damascene Al(Cu). <i>Materials Research Society Symposia Proceedings</i> , 1999 , 563, 91		1
17	Influence of temperature on the properties of sputtered AlSiCu films. <i>Applied Surface Science</i> , 1993 , 73, 295-304	6.7	1
16	3D total variation denoising in X-CT imaging applied to pore extraction in additively manufactured parts. <i>Measurement Science and Technology</i> , 2022 , 33, 045602	2	1
15	A Micro-Computed Tomography Comparison of the Porosity in Additively Fabricated CuCr1 Alloy Parts Using Virgin and Surface-Modified Powders. <i>Materials</i> , 2021 , 14,	3.5	1
14	A Detailed Study of a Novel Wafer Separation Method for Surface Sensitive MEMS Wafers. <i>Materials Research Society Symposia Proceedings</i> , 2012 , 1415, 1		О
13	A novel tomographic characterisation approach for sag and dross defects in metal additively manufactured channels. <i>Additive Manufacturing</i> , 2021 , 39, 101892	6.1	O

12	Melt pool feature analysis using a high-speed coaxial monitoring system for laser powder bed fusion of Ti-6Al-4 of	3.2	O
11	Temporary 0-Level MEMS Packaging Using a Heat Decomposable Sealing Ring. <i>Procedia Engineering</i> , 2011 , 25, 1497-1500		
10	Enabling poly-SiGe MEMS scaling by improving anchor strength and resistance. <i>Microelectronic Engineering</i> , 2011 , 88, 2420-2423	2.5	
9	Contact Resistivity of Laser Annealed SiGe for MEMS Structural Layers Deposited at 210°C. <i>Materials Research Society Symposia Proceedings</i> , 2011 , 1299, 1		
8	The dependence of stress induced voiding on line width studied by conventional and high resolution resistance measurements. <i>Microelectronics Reliability</i> , 1998 , 38, 1035-1040	1.2	
7	Low Thermal Budget Techniques For Controlling Stress In Si1-XGeX Deposited At 210°LC. <i>Materials Research Society Symposia Proceedings</i> , 2006 , 910, 14		
6	Ti-W-N Deposition Stress as a Function of Microstructure. <i>Materials Research Society Symposia Proceedings</i> , 1993 , 308, 51		
5	Poly SiGe, a Promising Material for MEMS Post-Processing on Top of Standard CMOS Wafers 2001 , 960	0-963	
4	Design of a Poly-SiGe Piezoresistive Pressure Sensor. <i>Springer Series in Advanced Microelectronics</i> , 2014 , 51-73	1	
3	Poly-SiGe as Piezoresistive Material. <i>Springer Series in Advanced Microelectronics</i> , 2014 , 25-49	1	
2	The Pressure Sensor Fabrication Process. Springer Series in Advanced Microelectronics, 2014, 75-99	1	
1	Sealing of Surface Micromachined Poly-SiGe Cavities. <i>Springer Series in Advanced Microelectronics</i> , 2014 , 101-126	1	